

# isc N-Channel MOSFET Transistor

## APT5010B2LL

#### **FEATURES**

- Drain Current –I<sub>D</sub>= 46A@ T<sub>C</sub>=25 °C
- · Drain Source Voltage-
  - : V<sub>DSS</sub>=500V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)}$  =0.1  $\Omega$  (Max)
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



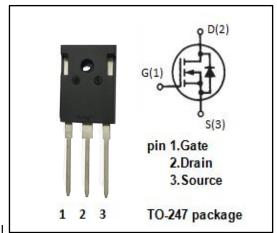
 Designed for use in switch mode power supplies and general purpose applications.

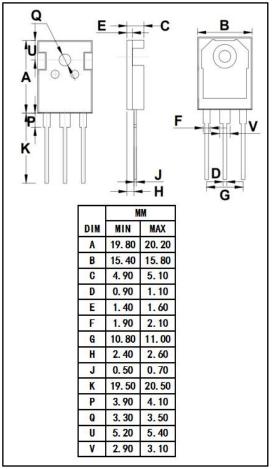
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                   | VALUE   | UNIT       |
|------------------|---|---------|------------|
| $V_{\text{DSS}}$ | Drain-Source Voltage                        | 500     | V          |
| V <sub>GS</sub>  | Gate-Source Voltage-Continuous ±30          |         | V          |
| I <sub>D</sub>   | Drain Current-Continuous 46                 |         | А          |
| I <sub>DM</sub>  | Drain Current-Single Pluse                  | 184     | А          |
| P <sub>D</sub>   | Total Dissipation @T <sub>C</sub> =25℃ 500  |         | W          |
| TJ               | Max. Operating Junction Temperature -55~150 |         | °C         |
| T <sub>stg</sub> | Storage Temperature                         | -55~150 | $^{\circ}$ |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | MAX  | UNIT |
|---------------------|--------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 0.25 | °C/W |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS   | MIN | MAX       | UNIT |
|----------------------|---------------------------------|--|-----|-----------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 500 |           | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | $V_{DS}$ = $V_{GS}$ ; $I_D$ = 2.5mA  | 3   | 5         | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> =23A   |     | 0.1       | Ω    |
| Igss                 | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0   |     | ±100      | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 400V; V <sub>GS</sub> = 0@T <sub>C</sub> =125°C |     | 25<br>250 | μА   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> =-46A; V <sub>GS</sub> = 0  |     | 1.3       | V    |

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